



### 20V N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	RDS(ON) Max	I <sub>D</sub> T <sub>A</sub> = +25°C
20V	$55m\Omega$ @ $V_{GS} = 4.5V$	4.6A
200	$100 \text{m}\Omega$ @ $V_{GS} = 2.5 \text{V}$	3.4A

### **Description**

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

# **Applications**

- DC-DC Converters
- Power Management Functions
- Backlighting

## **Features and Benefits**

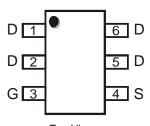
- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Mechanical Data**

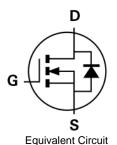
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Tin Finish Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.018 grams (Approximate)

# SOT26





Top View Pin Configuration



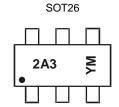
### Ordering Information (Note 4)

Part Number	Case	Packaging
ZXMN2A03F6TA	SOT26	3 000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



2A3 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: C = 2015) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Year	2015		2016	2017		2018	2019		2020	2021		2022
Code	С		D	Е		F	G		Н			J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	20	V
Gate-Source Voltage	$V_{GSS}$	±12	V
Continuous Drain Current, V <sub>GS</sub> = 10V	I <sub>D</sub>	4.6 3.7 3.7	А
Maximum Body Diode Forward Current (Note 6)	I <sub>S</sub>	2.7	Α
Pulsed Drain Current (Note 7)	I <sub>DM</sub>	16	A
Pulsed Source Current (Note 7)	I <sub>SM</sub>	16	А

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation Linear Derating Factor	T <sub>A</sub> = +25°C (Note 5)	P <sub>D</sub>	1.1 8.8	W mW/°C
Total Power Dissipation Linear Derating Factor	T <sub>A</sub> = +25°C (Note 6)	P <sub>D</sub>	1.7 13.6	W mW/°C
Thermal Resistance, Junction to Ambient	Steady State (Note 5)	Ъ	113	°C/W
Thermal Resistance, Junction to Ambient	Steady State (Note 6)	$R_{\theta JA}$	70	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

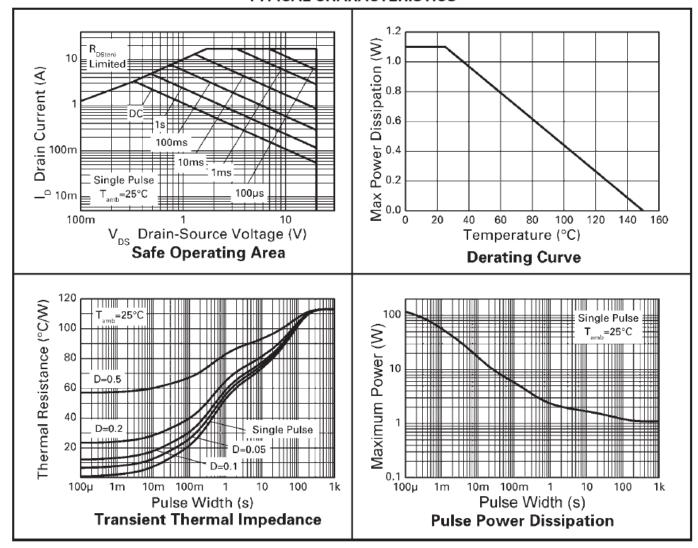
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.7	_	_	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance (Note 8)	D	_	_	55	mΩ	$V_{GS} = 4.5V, I_D = 7.2A$	
Static Dialii-Source Off-Resistance (Note 6)	R <sub>DS(ON)</sub>	_	_	100	11122	$V_{GS} = 2.5V, I_D = 4.6A$	
Diode Forward Voltage (Note 8)	$V_{SD}$	_	0.85	0.95	V	$V_{GS} = 0V, I_S = 4.1A$	
Forward Transconductance (Notes 8 & 10)	g <sub>fs</sub>	_	13	_	S	$V_{DS} = 10V, I_D = 7.2A$	
DYNAMIC CHARACTERISTICS (Note 10)	•				•		
Input Capacitance	C <sub>iss</sub>	_	837	_		V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V f = 1.0MHz	
Output Capacitance	Coss	_	168	_	pF		
Reverse Transfer Capacitance	Crss	_	90	_		1 = 1.0W112	
Total Gate Charge	Qg		8.2	_			
Gate-Source Charge	Q <sub>gs</sub>	_	2.3	_	nC	$V_{DS} = 10V$ , $I_D = 7.2A$ , $V_{GS} = 4.5V$	
Gate-Drain Charge	Q <sub>gd</sub>	_	2.0	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	4.7	_			
Turn-On Rise Time	t <sub>R</sub>	_	5.7	_	ns	$V_{GS} = 4.5V$ , $V_{DD} = 10V$ , $R_G = 6.0\Omega$ ,	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	18.5	_	115	I <sub>D</sub> = 1.0A	
Turn-Off Fall Time	t <sub>F</sub>		10.5	_			
Body Diode Reverse Recovery Time	t <sub>RR</sub>		12		ns	I <sub>F</sub> = 1.9A, dl/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>		4.9	_	nC	11 = 1.9A, αι/αι = 100A/μS	

Notes: 5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.

- 6. For a device surface mounted on FR-4 PCB measured at t  $\leq$ 5 secs.
- 7. Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.05, pulse width 10µs pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.
- 8. Measured under pulsed conditions. Width=300 $\mu$ s. Duty cycle  $\leq$  2%.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.

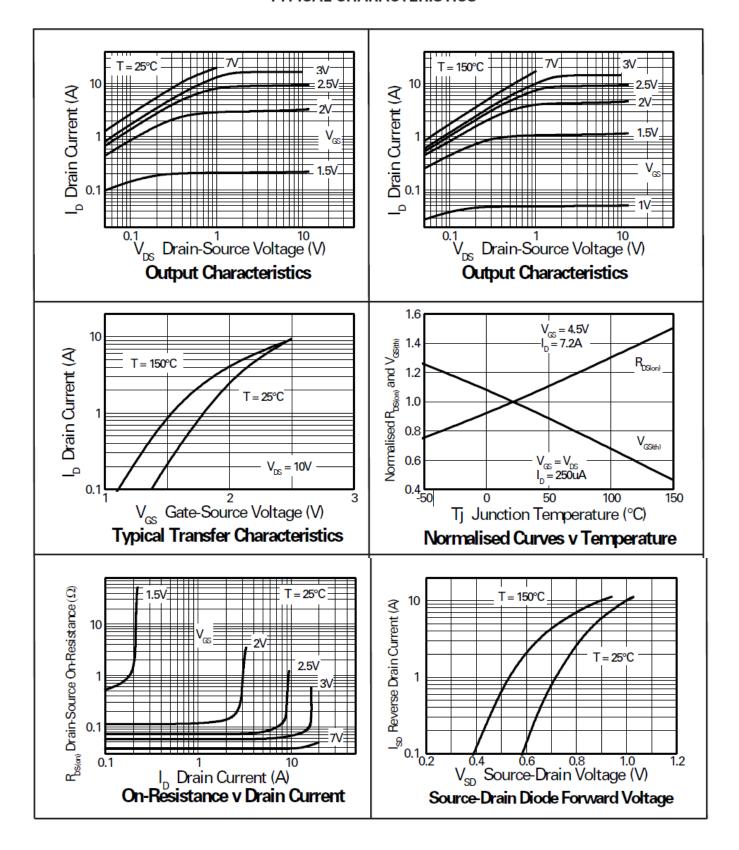


### TYPICAL CHARACTERISTICS



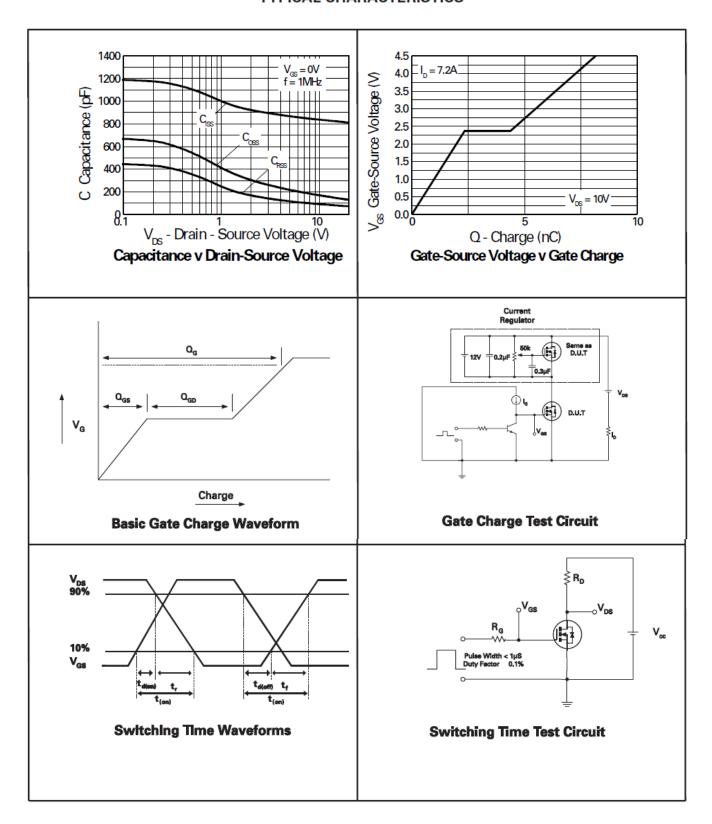


### TYPICAL CHARACTERISTICS





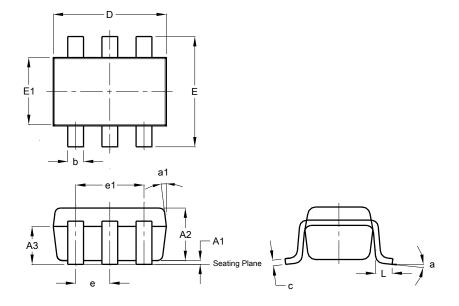
### TYPICAL CHARACTERISTICS





# **Package Outline Dimensions**

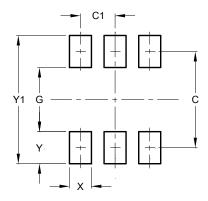
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT26							
Dim	Min	Max	Тур					
A1	0.013	0.10	0.05					
A2	1.00	1.30	1.10					
A3	0.70	0.80	0.75					
b	0.35	0.50	0.38					
С	0.10	0.20	0.15					
D	2.90	3.10	3.00					
е	-	-	0.95					
e1	-	-	1.90					
E	2.70	3.00	2.80					
E1	1.50	1.70	1.60					
L	0.35	0.55	0.40					
а	-	-	8°					
a1	-	-	7°					
All Dimensions in mm								

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



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